CGWT75N65F3EAD

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V_{CE}	Ic (Tc=100℃)	$V_{CE(sat)}$
650V	75A	1.63V

TO-247-3L



DESCRIPTION

The CGWT75N65F3EAD is used SZCJ 's third generation IGBT technology, has advanced Trench and FS(Field Stop) Structure，it's with high application frequent, low Collector-Emitter Saturation Voltage and switching loss, can easy to use in parallel.

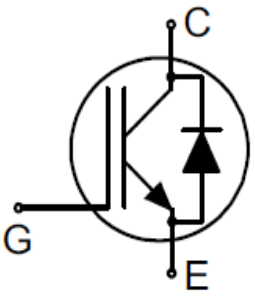
Features

- 650V breakdown Voltage
- Low Vce(sat) and positive temperature coefficient
- High speed switching，Low switching loss
- With fast and soft recovery freewheeling diode
- Good EMI behavior

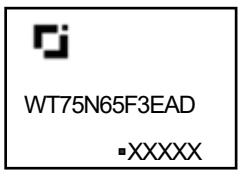
Application

- UPS application
- Solar Inverter
- Power Storage
- Servo

EQUIVALENT CIRCUIT



MARKING



WT75N65F3EAD = Device code
Solid dot = Green molding compound device, if none, the normal device
XXXXX = Code

Order Code	Package	Marking	Packing
CGWT75N65F3EAD	TO-247-3L	WT75N65F3EAD	Tube

感谢您的支持，如需要完整规格书，请联系：<igbt.list@szcjsemi.com >，谢谢!

Thank you for your support. If you need a complete datasheet, please contact:

<igbt.list@szcjsemi.com >. Thank you!